Notice of References Cited Application/Control No. | Applicant(s)/Patent Under Reexamination | ABADEER ET AL. | Examiner | Art Unit | Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	Α	US-2003/0020125	01-2003	Mandelman et al.	257/408
*	В	US-5,597,586	01-1997	Wilson et al.	425/67
*	С	US-5,654,218	08-1997	Lee, Bong Jae	438/301
*	D	US-5,241,203	08-1993	Hsu et al.	257/344
*	E	US-5,210,435	05-1993	Roth et al.	257/344
*	F	US-5,182,619	01-1993	Pfiester, James R.	257/382
	G	US-			
	Н	US-			
	ı	US-			
	J	US-			
	К	US-			
	L	US-			
	М	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	z					
	0					
	Ρ					
	α					
	R					
	S					
	T	77.				

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	u	Chen et al., "Self-Aligned Silicided Inverse-T Gate LDD Devices For Sub-Half Micron CMOS Technology", IEDM, 1990. Technical Digest., International, 9-12 Dec. 19, pages 829-832.
·	٧	
	w	
	х	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.